



JST04K-800TW 4A TRIACs

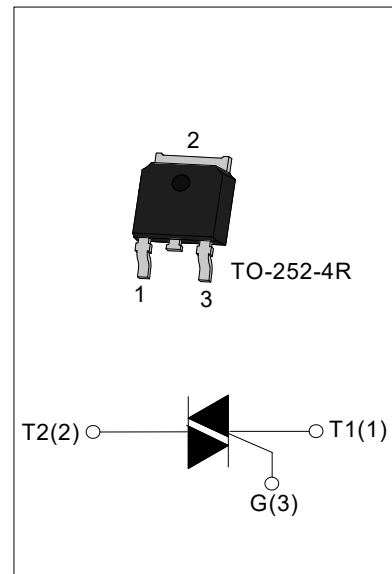
Rev.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JST04K-800TW triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, especially recommended for use on inductive load. Package TO-252-4R is RoHS compliant. (2011/65/EU)

MAIN FEATURES

Symbol	Value	Unit
V_{DRM}/V_{RRM}	800	V
$I_{T(RMS)}$	4	A



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40 - 150	°C
Operating junction temperature range		T_j	-40 - 125	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)		V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)		V_{RRM}	800	V
RMS on-state current	TO-252-4R ($T_c=100^\circ\text{C}$)	$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		I_{TSM}	40	A
I^2t value for fusing ($t_p=10\text{ms}$)		I^2t	8	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$)		di/dt	20	$\text{A}/\mu\text{s}$
Peak gate current		I_{GM}	4	A
Average gate power dissipation		$P_{G(AV)}$	1	W
Peak gate power		P_{GM}	5	W

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
I_{GT}	$V_D=12\text{V } R_L=33\Omega$	I - II -III	MAX	5	mA
V_{GT}		I - II -III	MAX	1.5	V
V_{GD}	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX	10	mA
		II		15	
I_H	$I_T=100\text{mA}$		MAX	10	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	50	V/ μs

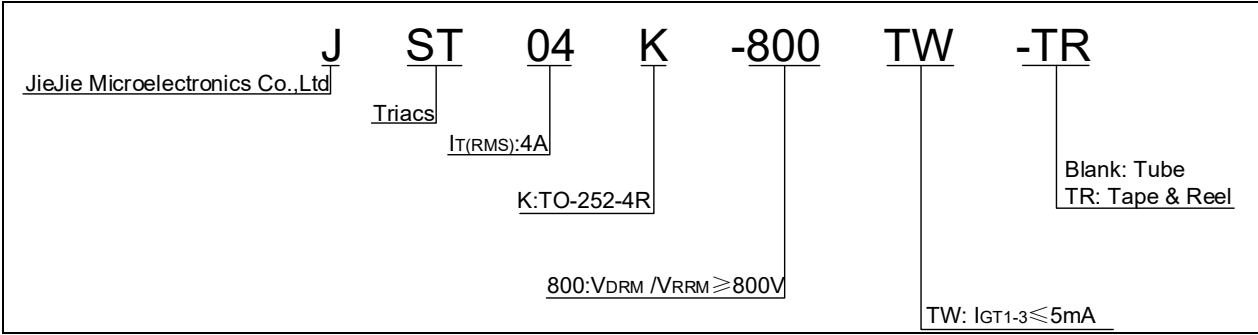
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX)	Unit
V_{TM}	$I_{TM}=5.5\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
V_{TO}	Threshold voltage	$T_j=125^\circ\text{C}$	0.93	V
R_d	Dynamic resistance	$T_j=125^\circ\text{C}$	97	m Ω
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	10	μA
I_{RRM}		$T_j=125^\circ\text{C}$	0.75	mA

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-252-4R	4.8	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient		70	

ORDERING INFORMATION



MARKING

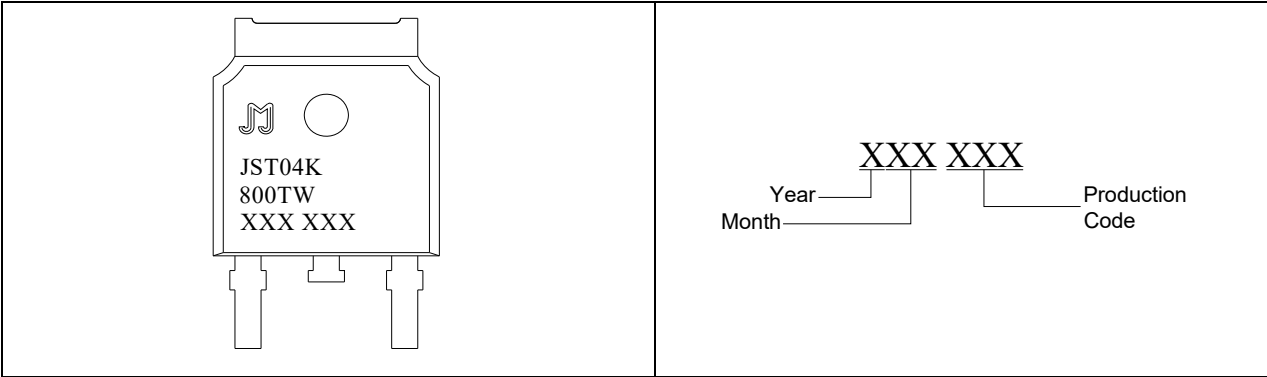


FIG.1: Maximum power dissipation versus RMS on-state current

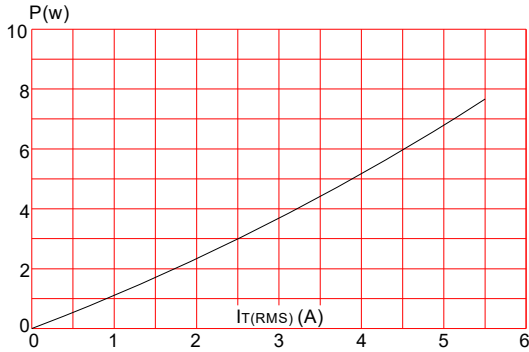


FIG.3: RMS on-state current versus case temperature

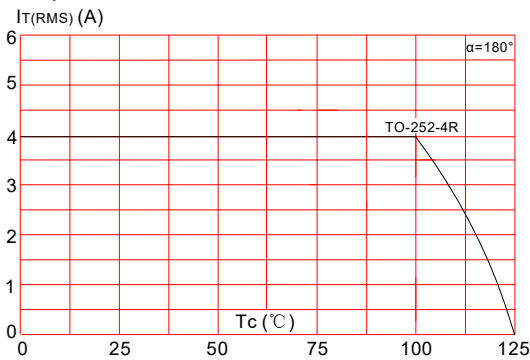


FIG.5: On-state characteristics (maximum values)

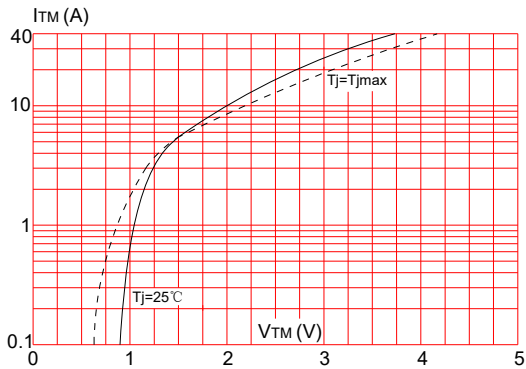


FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature

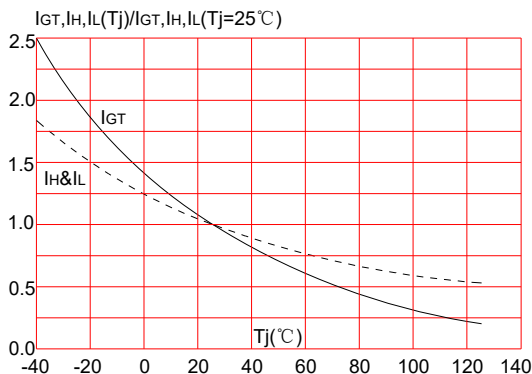


FIG.2: RMS on-state current versus ambient temperature (printed circuit board FR4, copper thickness:35µm)(full cycle)

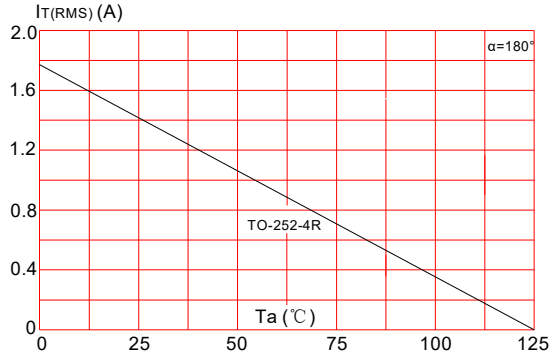


FIG.4: Surge peak on-state current versus number of cycles

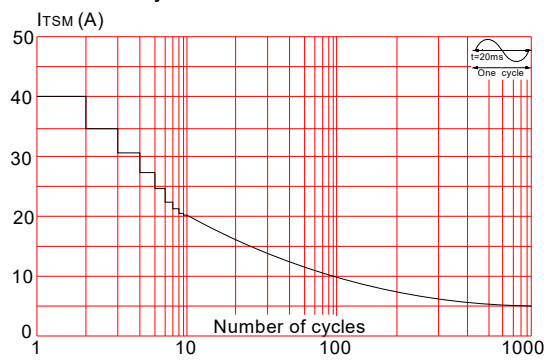
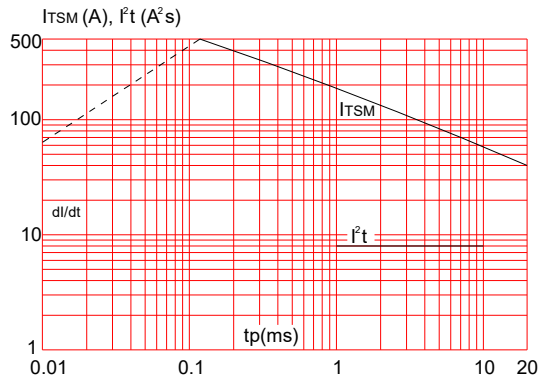
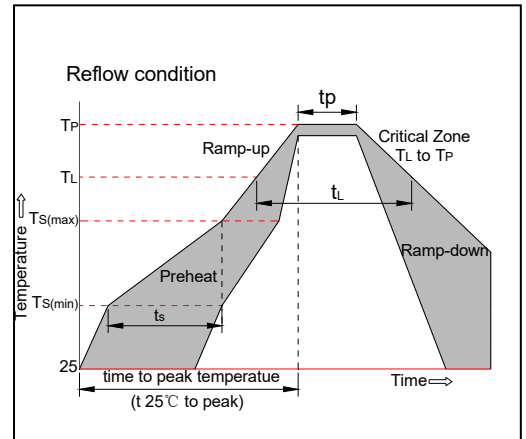


FIG.6: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($di/dt < 50\text{A}/\mu\text{s}$)



SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max ($T_{s(max)}$)	+200°C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L) (Liquidus)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C



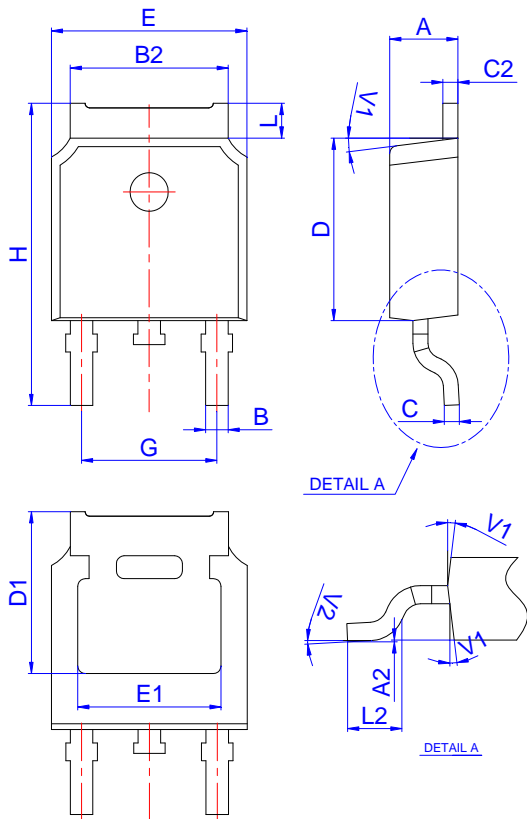
ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST04K-800TW	800	5	TO-252-4R	80	Tube
				2,500	Tape

Document Revision History

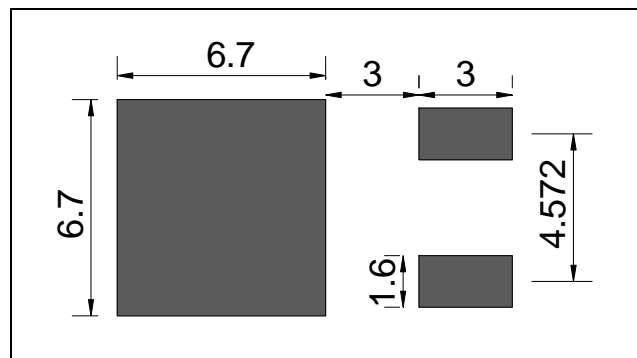
Date	Revision	Changes
Mar 27, 2022	1	Last update

PACKAGE MECHANICAL DATA

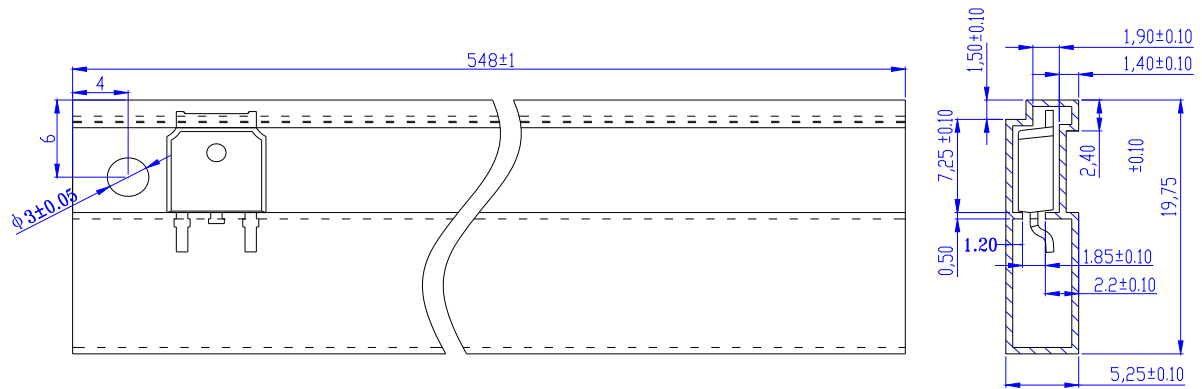


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

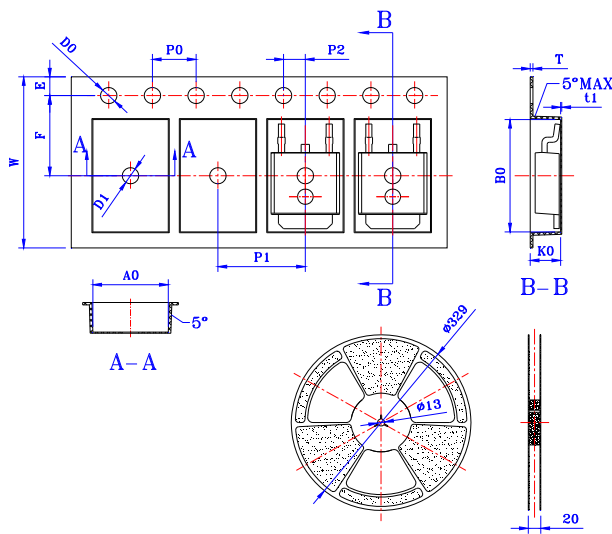
FOOTPRINT-TO-252-4R (dimensions in mm)



DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-252-4R	TUBE	80	4,000	20,000




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.90	7.00	0.270	0.272	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.106	0.109	0.113
T	0.24	-	0.27	0.009	-	0.011
t1	0.10	-	-	0.004	-	-

PACKAGE	OUTLINE	REEL (PCS)	PER CARTON (PCS)	TAPE & REEL
TO-252-4R	TAPING	2,500	25,000	13 inch



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